

Sub B1
A
c) an observation part including a pn junction irradiated with a laser beam to detect said fluctuation in potential, wherein:

1) said observation part includes a first MOS transistor having:

i) a source/drain region including a first impurity region of a first conductivity type, that is connected with said first end of said wire and that is formed within a second impurity region of a second conductivity type; and

ii) a first gate electrode that is electrically insulated from the second gate electrode; and

2) said pn junction includes said first impurity region.

Please cancel Claims 2-3 without prejudice or disclaimer.

4. (withdrawn from consideration)

Please cancel Claim 5 without prejudice or disclaimer.

Sub B2
A2
6. (Amended) The semiconductor device according to claim 1, wherein:
said portion measured is a gate electrode of said second MOS transistor.

7. (Amended) The semiconductor device according to claim 1, wherein:
said portion measured is a source/drain region of said second MOS transistor.

Claims 8-10. (withdrawn from consideration)

Sub B3
A3
11. (Amended) The semiconductor device according to claim 1, wherein:

a) said first conductivity type is an n type and said second conductivity type is a p type;

b) said observation part further includes:

1) a second pn junction having a p-type third impurity region connected with said wire; and